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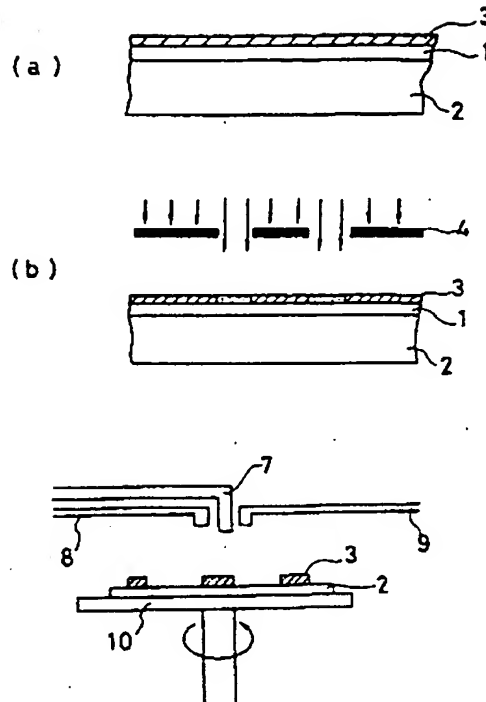
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TITLE : PRODUCTION OF SEMICONDUCTOR
DEVICE



ABSTRACT : **PURPOSE:** To completely remove the scum of a developing soln. and resist by adopting two-stages processing of cleaning by an aq. alcohol soln. and cleaning by pure water in a stage for rinsing the photoresist pattern applied on a semiconductor substrate and subjected to exposing and developing.

CONSTITUTION: The photoresist 3 is applied on the semiconductor substrate 2 on which a film 1 such as silicon oxide film or polycrystalline silicon film is formed. The photoresist is subjected to soft baking at a prescribed temp. The photoresist 3 is then exposed by UV irradiation using a photomask 4 and is developed by the developing soln. The resist pattern is formed after this resist is subjected to the rinsing stage. The rinsing is executed by first injecting the aq. alcohol soln. from a nozzle 8 onto the substrate 2 while rotating the substrate, then by injecting the pure water from a nozzle 9 to clean the resist pattern with the pure water. The rotating speed of the substrate is increased after two stages of said cleaning and the substrate is subjected to spin drying. The resist pattern is thus formed without having the remaining developing soln. and the resist scum. The yield and reliability of the semiconductor device are, therefore, improved.

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